

isc Silicon NPN Power Transistor

2SCR586D

DESCRIPTION

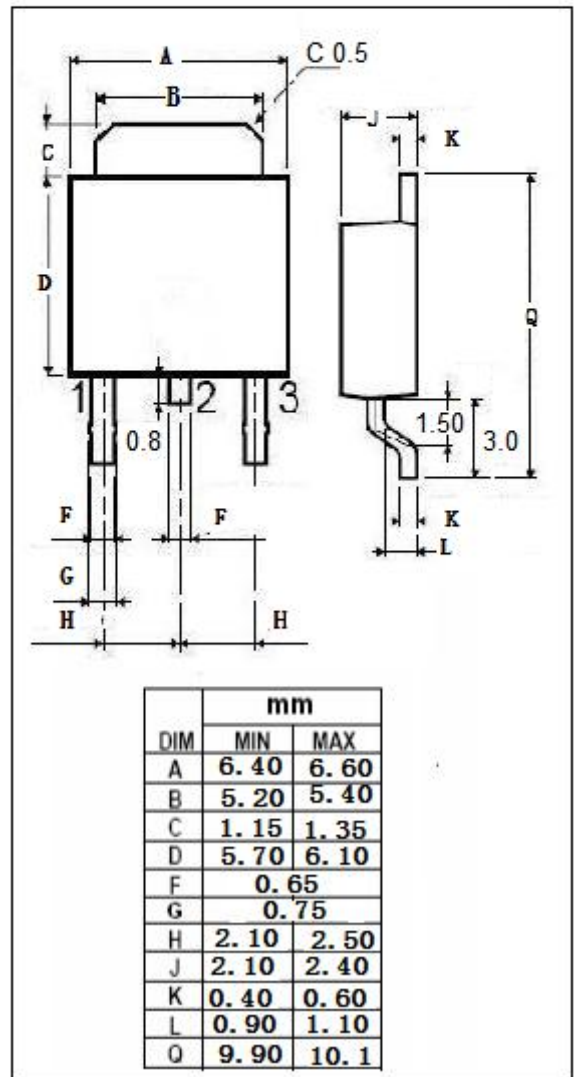
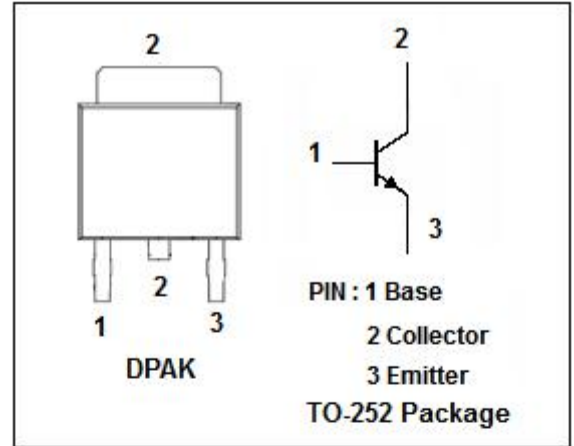
- Suitable for middle power drivers
- Low $V_{CE(sat)}$
 $V_{CE(sat)} \leq 0.3V @ (I_C=2A, I_B=100mA)$
- Complementary NPN types: 2SAR586D
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Low frequency amplifier

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	10	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon NPN Power Transistor**2SCR586D****ELECTRICAL CHARACTERISTICS**T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
BV _{CBO}	Collector-Base breakdown voltage	I _C =100uA	80			V
BV _{CEO}	Collector-Emitter breakdown voltage	I _C =1mA	80			V
BV _{EBO}	Emitter-Base breakdown voltage	I _E =100uA	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 100mA			0.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 80V; I _E = 0			1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			1.0	μ A
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 3V	120		390	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1.0MHz		50		pF
f _T ^{NOTE}	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 10V,f= 100MHz		200		MHz

NOTE:Pulsed